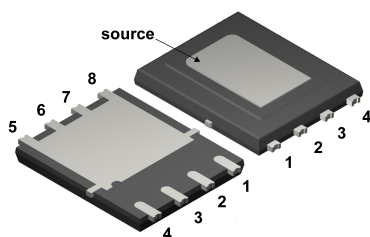
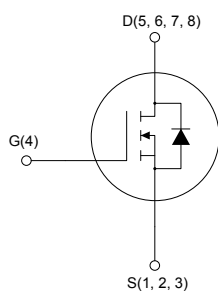


Automotive-grade N-channel 40 V, 0.82 mΩ typ., 120 A, STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 DSC package



PowerFLAT™ 5x6 dual side cooling



AM15540v4



Product status link

[STLD257N4F7AG](#)

Product summary

Order code	STLD257N4F7AG
Marking	257
Package	PowerFLAT™ 5x6 dual side cooling
Packing	Tape and reel

Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STLD257N4F7AG	40 V	1.1 mΩ	120 A

- AEC-Q101 qualified 
- Among the lowest R_{DS(on)} on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness
- Wettable flank package

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)(2)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(1)(2)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	480	A
$P_{TOT}^{(2)}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	158	W
T_J	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Limited by package
2. The value is rated according to $R_{thj\text{-case}}$ bottom side.
3. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-c top side}}$	Thermal resistance junction-case top side	2.90	$^\circ\text{C/W}$
$R_{thj\text{-c bottom side}}$	Thermal resistance junction-case bottom side	0.95	
$R_{thj\text{-pcb}}^{(1)}$	Thermal resistance junction-pcb	31.3	

1. When mounted on an 1-inch² 2 Oz, Cu board, $t \leq 10\text{ s}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	50	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 25\text{ V}$)	608	mJ

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	40			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 40\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 16\text{ V}$, $T_j = 125\text{ }^{\circ}\text{C}^{(1)}$			300	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$		0.82	1.1	m Ω
		$V_{GS} = 6.5\text{ V}$, $I_D = 60\text{ A}$		3.1	4.8	

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	5400	-	pF
C_{oss}	Output capacitance		-	1870	-	pF
C_{rss}	Reverse transfer capacitance		-	45	-	pF
Q_g	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	66.5	-	nC
Q_{gs}	Gate-source charge		-	33.5	-	nC
Q_{gd}	Gate-drain charge		-	13	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 60\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	28	-	ns
t_r	Rise time		-	19	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	58	-	ns
t_f	Fall time		-	32	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		120	A
$I_{SDM}^{(1)(2)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 90\text{ A}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 120\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	54		ns
Q_{rr}	Reverse recovery charge		-	53		nC
I_{RRM}	Reverse recovery current		-	1.9		A

1. Limited by package.
2. Pulse width is limited by safe operating area.
3. Pulse test: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

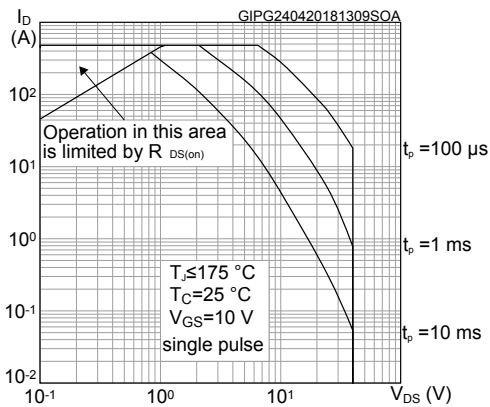


Figure 2. Thermal impedance

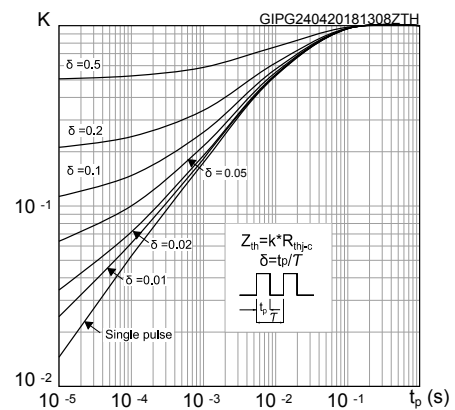


Figure 3. Output characteristics

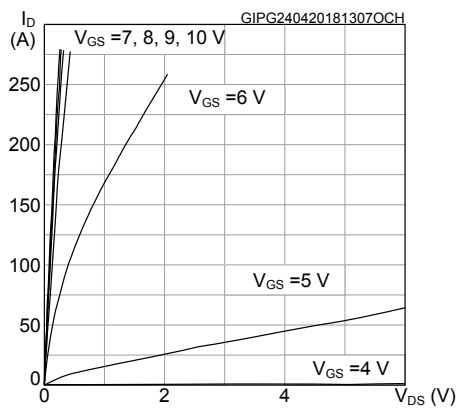


Figure 4. Transfer characteristics

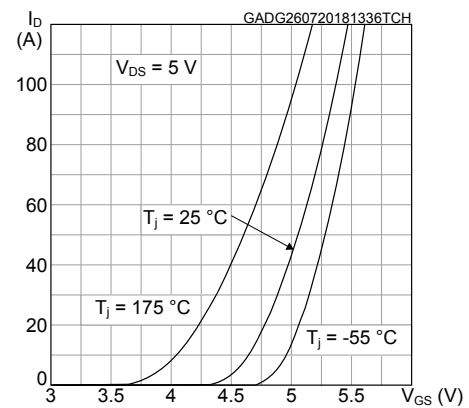


Figure 5. Gate charge vs gate-source voltage

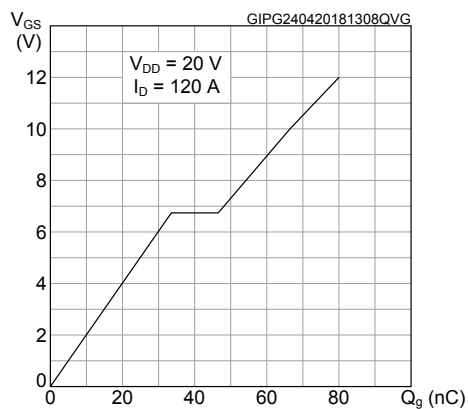


Figure 6. Static drain-source on-resistance

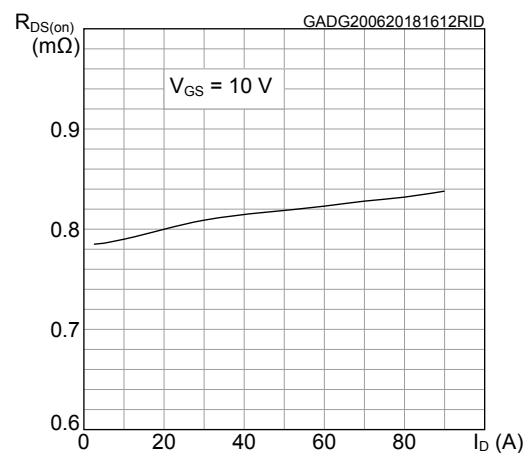


Figure 7. Capacitance variations

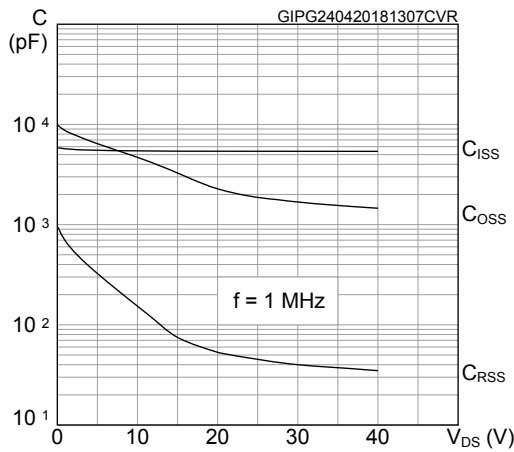


Figure 8. Normalized gate threshold voltage vs temperature

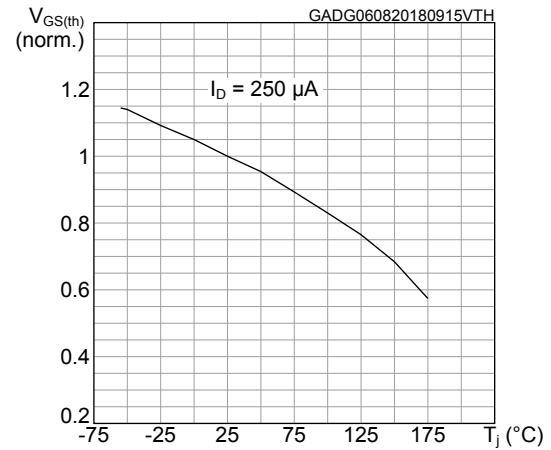


Figure 9. Normalized on-resistance vs temperature

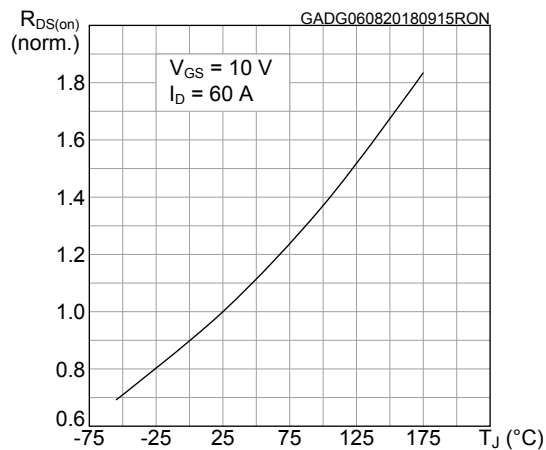


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

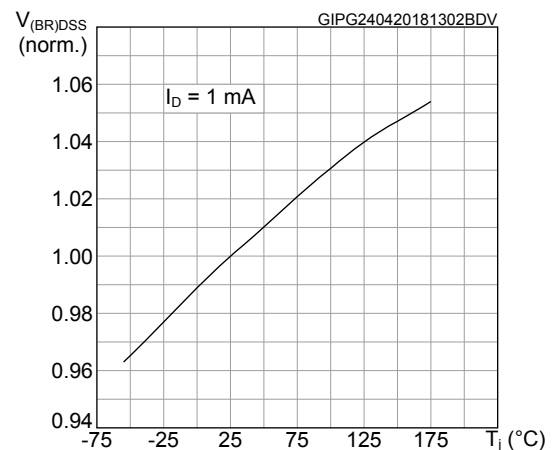
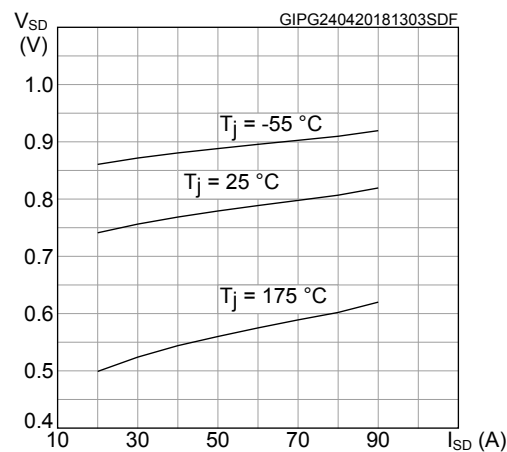
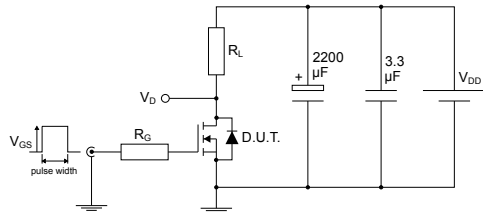


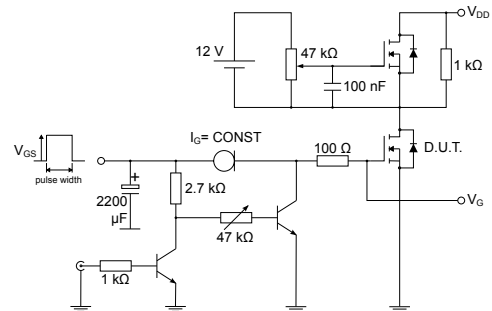
Figure 11. Source-drain diode forward characteristics



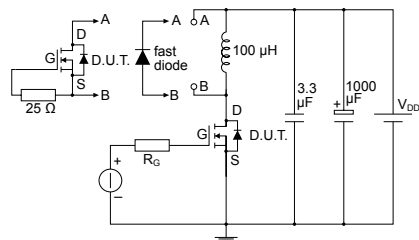
3 Test circuits

Figure 12. Test circuit for resistive load switching times


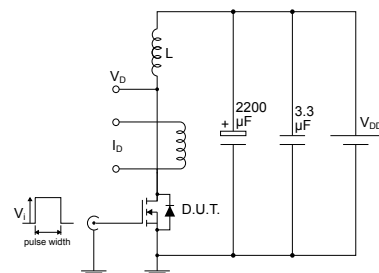
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Figure 13. Test circuit for gate charge behavior


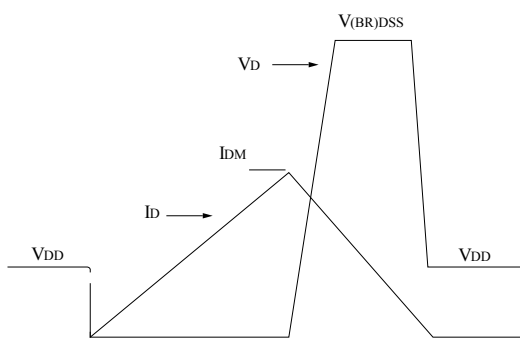
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Figure 14. Test circuit for inductive load switching and diode recovery times


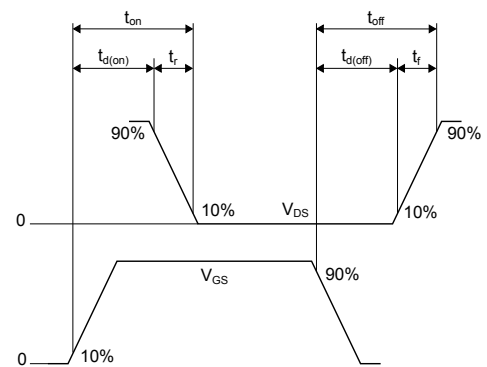
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Figure 15. Unclamped inductive load test circuit


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Figure 16. Unclamped inductive waveform


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Figure 17. Switching time waveform


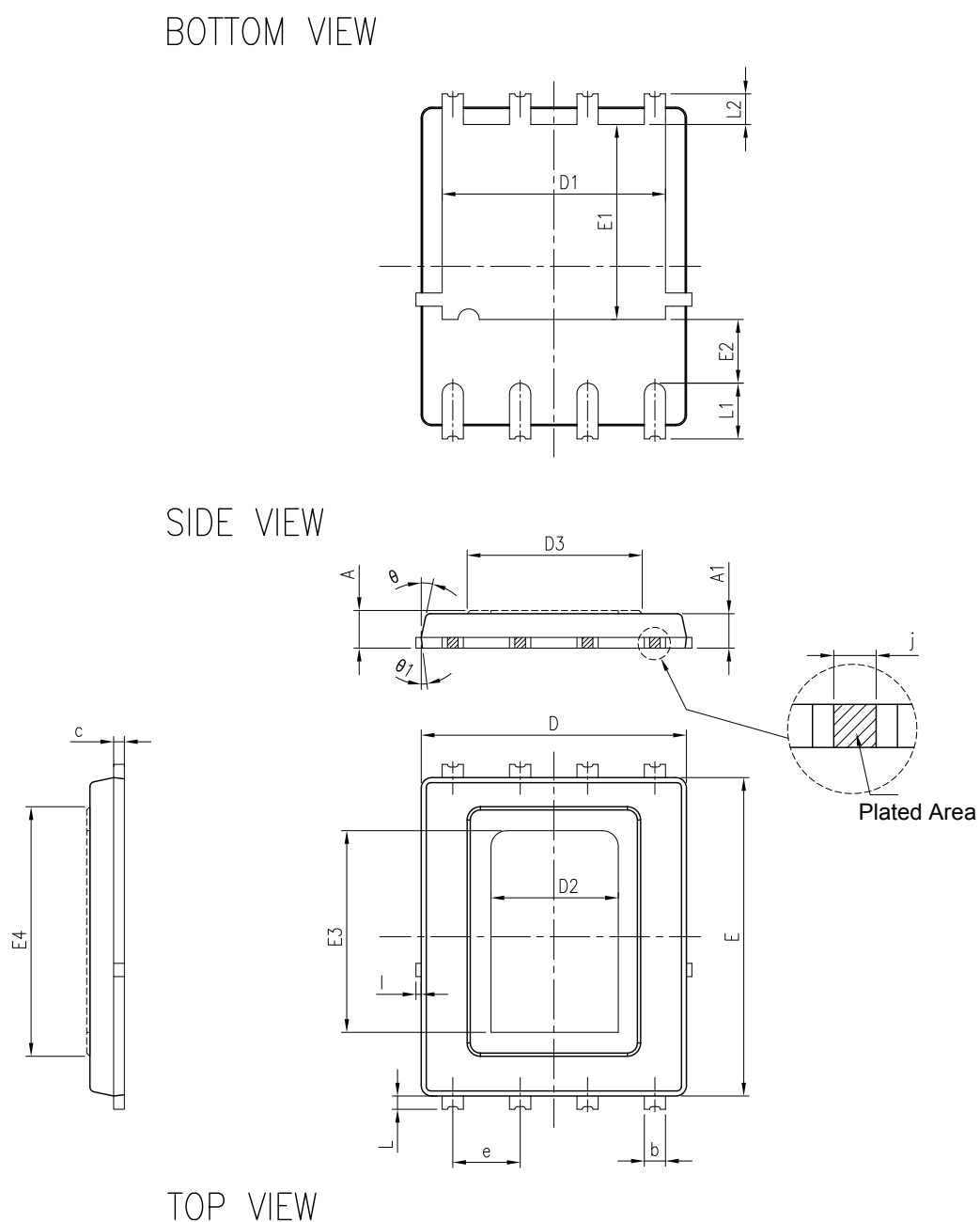
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT™ 5x6 dual side cooling package information

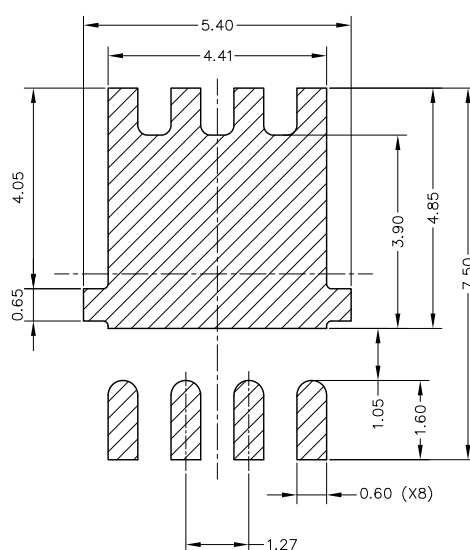
Figure 18. PowerFLAT™ 5x6 dual side cooling package outline



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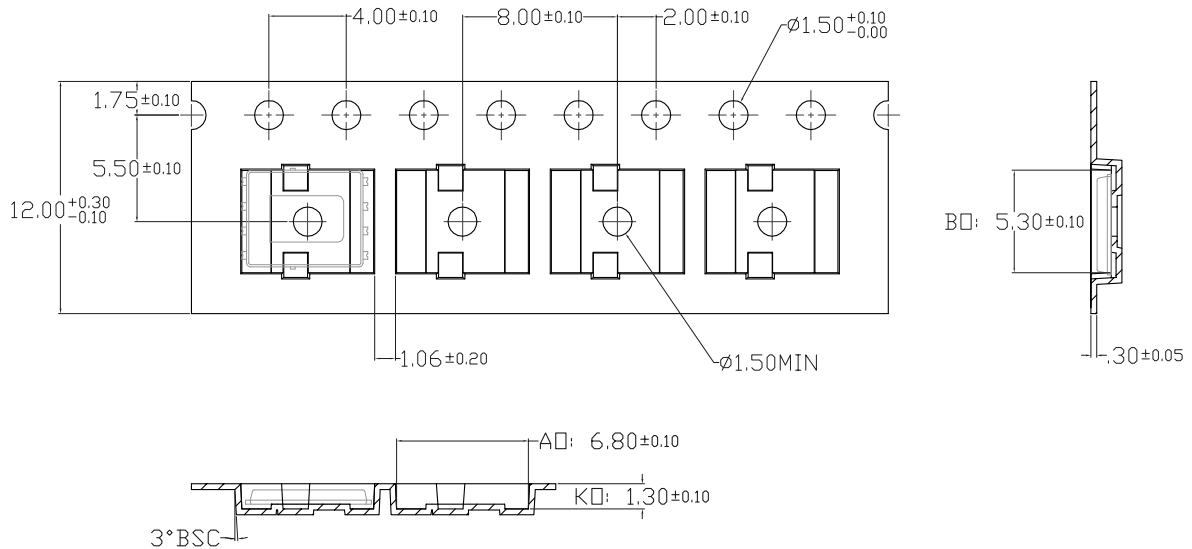
Table 8. PowerFLAT™ 5x6 dual side cooling mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.66	0.71	0.76
A1	0.60		0.75
b	0.33	0.43	0.53
c	0.15	0.203	0.30
D	5.00 BSC		
D1	4.06	4.21	4.36
D2	2.40 BSC		
D3	2.80	3.30	3.80
E	6.00 BSC		
E1	3.525	3.675	3.825
E2	1.05	1.20	1.35
E3	3.80 BSC		
E4	4.20	4.70	5.20
e	1.27 BSC		
l			0.15
L	0.15	0.25	0.35
L1	0.925	1.05	1.175
L2	0.45	0.575	0.70
ϑ	12° BSC		
ϑ1	7° BSC		
j	0.20 BSC		

Figure 19. PowerFLAT™ 5x6 dual side cooling recommended footprint (dimensions are in mm)


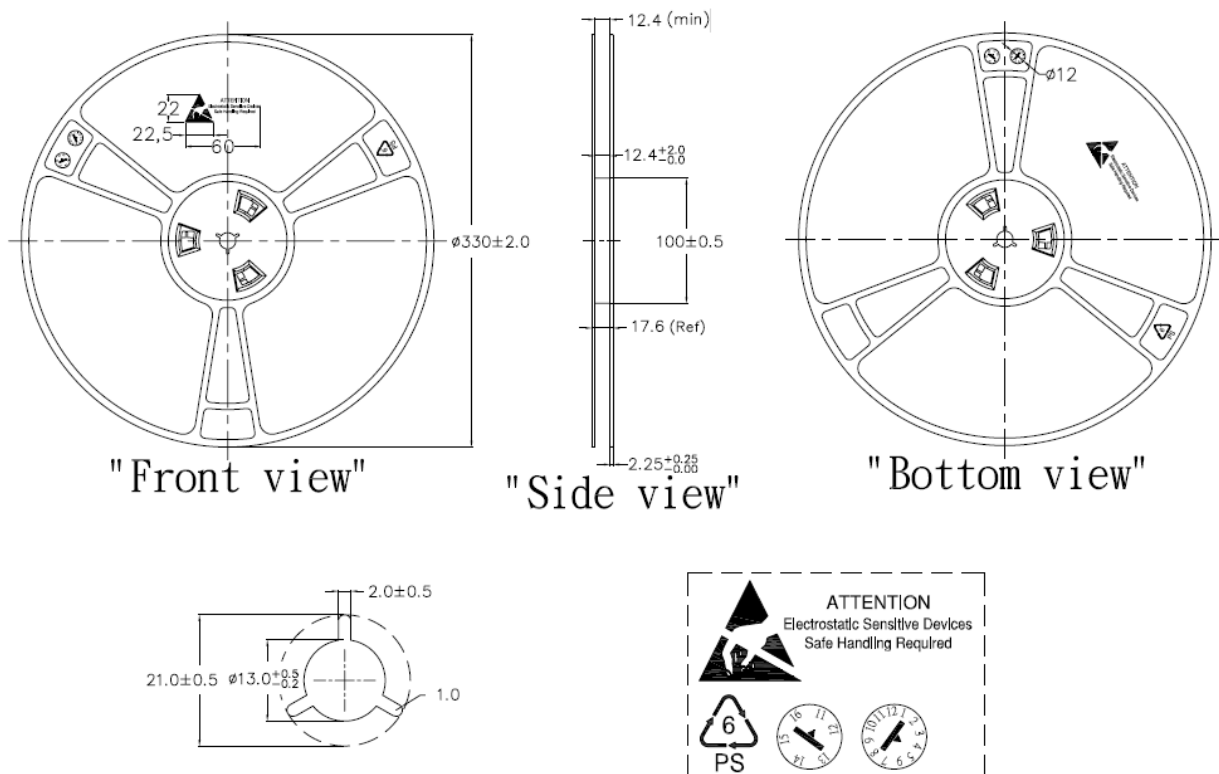
4.2 PowerFLAT™ 5x6 dual side cooling packing information

Figure 20. PowerFLAT™ 5x6 dual side cooling tape (dimensions are in mm)



8548087_REV1

Figure 21. PowerFLAT™ 5x6 dual side cooling reel (dimensions are in mm)



Revision history

Table 9. Document revision history

Date	Revision	Changes
02-May-2018	1	Initial release.
26-Jul-2018	2	Document status promoted from preliminary to production data. Updated <i>Table 4. On/off states</i> . Updated <i>Section 2.1 Electrical characteristics (curves)</i> . Minor text changes
6-Aug-2018	3	Updated <i>Table 5. Dynamic</i> . Updated <i>Section 2.1 Electrical characteristics (curves)</i> Minor text changes
21-Mar-2019	4	Modified <i>Table 4. On/off states</i> . Modified <i>Figure 1. Safe operating area</i> , <i>Figure 4. Transfer characteristics</i> , <i>Figure 6. Static drain-source on-resistance</i> and <i>Figure 9. Normalized on-resistance vs temperature</i> . Minor text changes.

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